

Supplementary Information

Room-Temperature, Solution-Processable Organic Electron Extraction Layer for High-Performance Planar Heterojunction Perovskite Solar Cells

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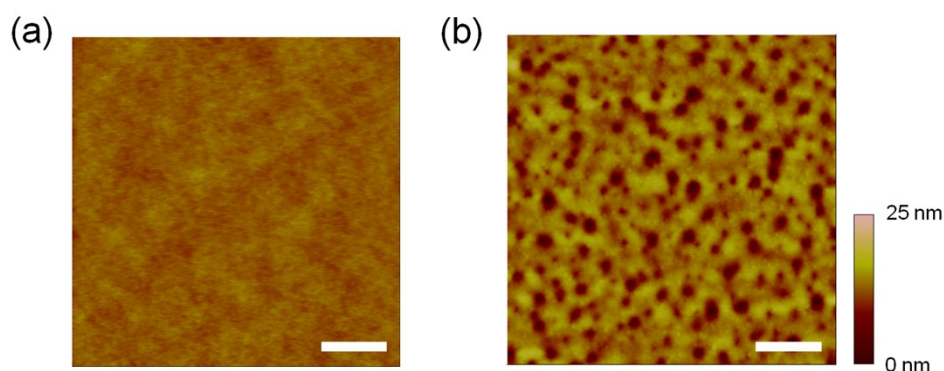


Figure S1. Atomic force microscopy images of FPI-PEIE and PC₆₁BM on FPI-PEIE (scale bar: 1 μm).

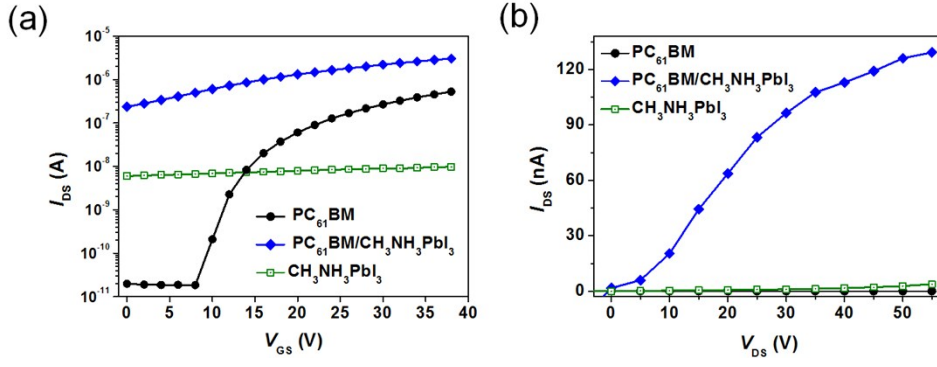


Figure S2. (a) Transfer characteristics of field-effect transistors based on pristine PC₆₁BM (circles), pristine CH₃NH₃PbI₃ (squares) and PC₆₁BM/CH₃NH₃PbI₃ (diamonds), and (b) output characteristics of field-effect transistors based on pristine PC₆₁BM (circles), pristine CH₃NH₃PbI₃ (squares) and PC₆₁BM/ CH₃NH₃PbI₃ (diamonds) at zero gate voltage.

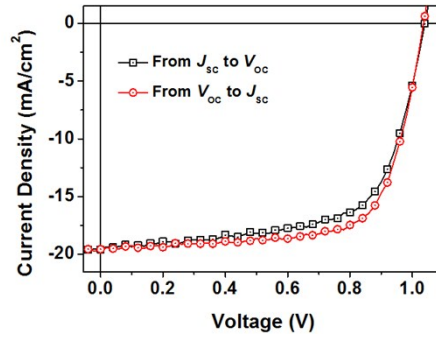


Figure S3. J - V characteristics of the studied CH₃NH₃PbI₃ solar cell based on FPI-PEIE/PC₆₁BM layer under AM 1.5G irradiation at 100 mW cm⁻². The scan rate is 0.05 V s⁻¹.

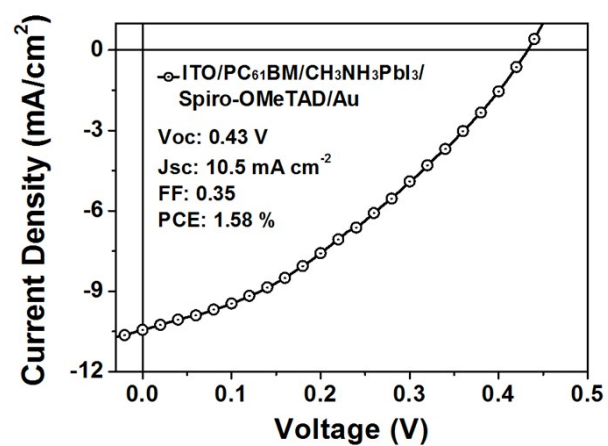


Figure S4. J - V characteristics of the control perovskite solar cell using a single PC₆₁BM layer as the EEL under AM 1.5G irradiation at 100 mW cm⁻².